

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT PTO-1449</b>	Docket No. <b>52433/858</b>	Application No. <b>10/589,680</b>	
	Applicant(s) <b>Masashi NAKABAYASHI et al.</b>	Examiner <b>Jonathan C. Langman</b>	
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## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT/PUBLICATION NUMBER	PATENT/PUBLICATION DATE mm/dd/yyyy	NAME	CLASS	SUBCLASS	FILING DATE
/JL/	5,856,231	01/05/1999	Niemann et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE mm/dd/yyyy	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						Yes	No
/JL/	9-500861	01/28/97	Japan			corresponds to US Patent No. 5,856,231	

## OTHER DOCUMENTS

EXAMINER INITIAL	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
/JL/	Yu. M. Tairov et al. "General Principles of Growing Large-Size Single Crystals of Various Silicon Carbide Polytypes" Journal of Crystal Growth 52 (1981) 146-150
/JL/	S.A. Reshanov et al., "Features of Semi-Insulating SiC Single-Crystal Growth by Physical Vapor Transport" Materials Science Forum Vols. 353-356 (2001) pp 53-56
/JL/	M. Bickermann et al., "On the Preparation of Vanadium-Doped Semi-Insulating SiC Bulk Crystals" Materials Science Forum Vols. 389-393 (2002) pp. 139-142
/JL/	M.E. Zvanut et al. "The level position of a deep intrinsic defect in 4H-SiC studied by photoinduced electron paramagnetic resonance." Applied Physics Letters. Volume 80, Number 3. 21 January 2002 pp 410-412.
/JL/	B. Magnusson et al. "Properties of the UD-1 Deep-Level Center in 4H-SiC" Materials Science Forum Vols. 389-393 (2002) pp 505-508
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EXAMINER /Jonathan Langman/	DATE CONSIDERED 11/25/2009
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	